

2.5V Drive Nch MOSFET

RSM002N06

Structure

Silicon N-channel MOSFET

Features

- 1) High speed switing.
- 2) Small package(VMT3).
- 3) Low voltage drive(2.5V drive).

Application

Switching

Packaging specifications

	Package	Taping	
Type	Code	T2L	
	Basic ordering unit (pieces)	8000	
RSM002N0	0		

• Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I _D	±250	mA
	Pulsed	I _{DP} *1	±1	Α
Source current	Continuous	I _S	125	mA
(Body Diode)	Pulsed	I _{SP} *1	1	Α
Power dissipation		P _D *2	150	mW
Channel temperature		Tch	150	°C
Range of storage temperature		Tstg	-55 to +150	°C

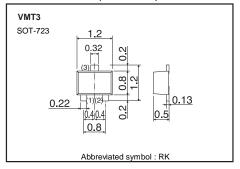
^{*1} Pw≤10µs, Duty cycle≤1%

• Thermal resistance

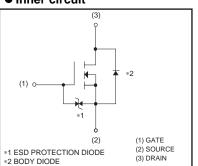
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W

^{*} Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



• Inner circuit



^{*2} Each terminal mounted on a recommended land.

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	$V_{GS}=\pm20V, V_{DS}=0V$
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V_{DS} =60V, V_{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.3	٧	$V_{DS}=10V$, $I_{D}=1mA$
		1	1.7	2.4	Ω	I _D =250mA, V _{GS} =10V
Static drain-source on-state	R _{DS (on)}	1	2.1	3.0		I _D =250mA, V _{GS} =4.5V
resistance		1	2.3	3.2		I _D =250mA, V _{GS} =4.0V
		1	3.0	12.0		I _D =10mA, V _{GS} =2.5V
Forward transfer admittance	I Y _{fs} I*	0.25	-	-	S	I _D =250mA, V _{DS} =10V
Input capacitance	C _{iss}	1	15	-	pF	V _{DS} =25V
Output capacitance	C _{oss}	1	4.5	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	1	2.0	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	3.5	-	ns	I _D =100mA, V _D ; 30V
Rise time	t _r *	-	5	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	-	18	-	ns	R _L ≒300Ω
Fall time	t _f *	-	28	-	ns	$R_G=10\Omega$

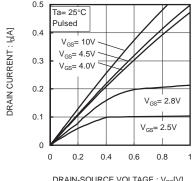
^{*}Pulsed

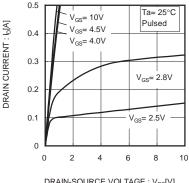
●Body diode characteristics (Source-Drain) (Ta = 25°C)

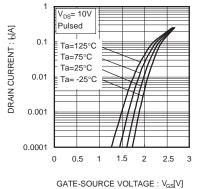
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V _{SD} *	-	-	1.2	V	I_s =250mA, V_{GS} =0V

^{*}Pulsed

•Electrical characteristic curves





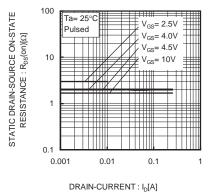


DRAIN-SOURCE VOLTAGE : V_{DS}[V]

Fig.1 Typical Output Characteristics(I)

$$\begin{split} & \text{DRAIN-SOURCE VOLTAGE}: V_{\text{DS}}[V] \\ & \text{Fig.2 Typical Output Characteristics(II)} \end{split}$$

Fig.3 Typical Transfer Characteristics



Ta=125°C
Ta=75°C
Ta=25°C
Ta=-25°C
Ta=-25°C
Ta=-25°C
Ta=-25°C
Ta=-25°C

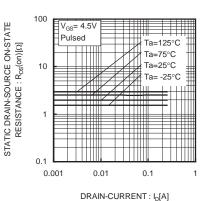
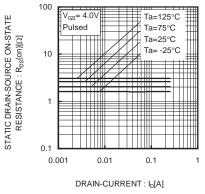
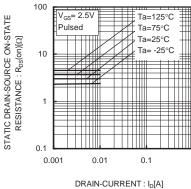


Fig.4 Static Drain-Source On-State Resistance vs. Drain Current(1)

DRAIN-CURRENT : I_D[A]
Fig.5 Static Drain-Source On-State
Resistance vs. Drain Current(II)

Fig.6 Static Drain-Source On-State Resistance vs. Drain Current(III)





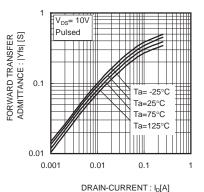
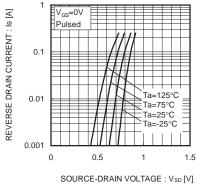


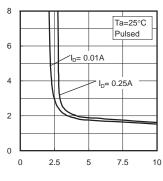
Fig.7 Static Drain-Source On-State Resistance vs. Drain Current(IV)

Fig.8 Static Drain-Source On-State
Resistance vs. Drain Current(IV)

Fig.9 Forward Transfer Admittance vs. Drain Current







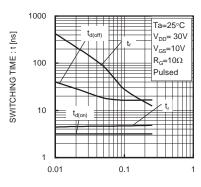


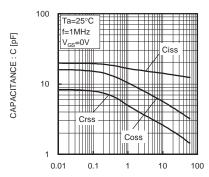
Fig.10 Reverse Drain Current

Fig.10 Reverse Drain Current vs. Sourse-Drain Voltage

GATE-SOURCE VOLTAGE : V_{GS}[V]
Fig.11 Static Drain-Source On-State

Resistance vs. Gate Source Voltage

 $\begin{aligned} & \mathsf{DRAIN\text{-}CURRENT:I_{D}[A]} \\ & \mathsf{Fig.12} \; \mathsf{Switching} \; \mathsf{Characteristics} \end{aligned}$



DRAIN-SOURCE VOLTAGE : VDS[V]
Fig.13 Typical Capacitance
vs. Drain-Source Voltage

●Measurement circuits

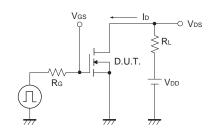


Fig.1-1 Switching time measurement circuit

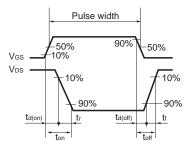


Fig.1-2 Switching waveforms

●Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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